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	Filing Date		2004-12-24	
	First Named Inventor	YANSON et al.		
	Art Unit	2828		
	Examiner Name	Not Yet Assigned		
Attorney Docket Number		35832.000130		

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/A.P./	1	YI, H. et al., "Effect of dielectric and semiconductor cap layer combinations in impurity free vacancy disordering of an InGaAs/InGaAsP single quantum well structure", Sae Mulli. Vol. 41, pp.193-8 (Sept. 2000) (Korean language version only available)	<input type="checkbox"/>
/A.P./	2	NG, S. et al., "Polarisation -dependent performance of multiple wavelength electro-absorption intensity modulator arrays on a single InGaAs/InGaAsP chip", LEOS, pp. 40 - 41 (2001)	<input type="checkbox"/>
/A.P./	3	SU, Y. et al., "Effects of In/sub0.53/Ga/sub0.47 cap layer and stoichiometry of dielectric capping layers on impurity-free vacancy disordering of In/sub 0.53 Ga/sub 0.47/As/InP multiquantum well structures", J. Appl. Phys. 88:5720-3 (2000)	<input type="checkbox"/>
/A.P./	4	NG, S. et al., "A low-cost solution in generating multiple-bandgaps for 1.55 μ m optical fibre communications", IEEE Lasers and Electro Optics Soc. (LEOS), pp. 626-7 (2001)	<input type="checkbox"/>
/A.P./	5	ONG, T. et al., "Fabrication of multiple-wavelength lasers in InGaAs-InGaAsP structures using direct laser writing", IEEE Photonics Technology Letters 13:1161-3 (Nov. 2001)	<input type="checkbox"/>
/A.P./	6	ONG, T. et al., "Wavelength tuning in InGaAs/InGaAsP quantum well lasers using pulsed-photoabsorption-induced disordering", Appl. Phys. Letters 78:2637-9 (2001)ONG, T. et al., "Wavelength tuning in InGaAs/InGaAsP quantum well lasers using pulsed-photoabsorption-induced disordering", Appl. Phys. Letters 78:2637-9 (2001)	<input type="checkbox"/>
/A.P./	7	SUDOHI, T. et al., "Wavelength trimming of distributed-feedback lasers by photo-absorption-induced disordering", Conference Proceedings LEOS '96 9th Annual Meeting IEEE Lasers and Electro Optics Soc. pp. 419-20 (1996)	<input type="checkbox"/>
/A.P./	8	Corrected Version of International Search Report by European Patent Office acting as ISA for International Application No. PCT/GB2004/005452, Mailed 12 August 2005.	<input type="checkbox"/>
/A.P./	9	Corrected Version of Written Opinion of International Searching authority, European Patent Office acting as ISA, for International Application No. PCT/GB2004/005452, mailed 12 August 2005.	<input type="checkbox"/>
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